

**A. Amendments to the Claims**

Please amend the claims as follows:

1. (Original) A method for fabricating an electrical circuit, comprising the steps of:  
depositing a layer of a first conductive material onto a surface of a substrate;  
depositing a layer of a second conductive material onto said layer of a first conductive material;  
  
selectively etching a portion of said layer of a second conductive material; and  
  
selectively etching a portion of said layer of a first conductive material.
2. (Currently amended) The method of ~~claim 1~~ claim 1 wherein said layer of first conductive material is substantially transparent.
3. (Original) The method of claim 1 wherein said first conductive material is indium tin oxide.
4. (Original) The method of claim 1 wherein said second conductive material is copper.
5. (Original) The method of claim 4 further comprising the step of electrically connecting an electrical component to said second conductive material.

6. (Original) The method of claim 5 wherein said step of electrically connecting said electrical component to said second conductive material comprises soldering said electrical component to said second conductive material.
7. (Original) The method of claim 1 further comprising the step of depositing a layer of a third conductive material onto said layer of second conductive material.
8. (Original) The method of claim 7 wherein said layer of second conductive material is substantially transparent.
9. (Original) The method of claim 7 wherein said second conductive material is an oxide of niobium.
10. (Original) The method of claim 7 wherein said third material is copper.
11. (Original) The method of claim 7 further comprising the step of electrically connecting an electrical component to said second conductive material.
12. (Original) The method of claim 11 wherein said step of electrically connecting said electrical component to said second conductive material comprises soldering said electrical component to said second conductive material.
13. (Original) The method of claim 1 wherein at least one of said steps of depositing occur in a substantial vacuum.

14. (Original) The method of claim 1 further comprising the step of pretreating said surface of said substrate to enhance adhesion of said layer of first conductive material to said substrate.

15. (Original) A method for fabricating an electrical circuit, comprising the steps of:  
depositing a layer of a first conductive material onto a surface of a substrate;  
depositing a layer of a second conductive material onto said layer of a first conductive material;  
selectively etching a first portion of said layer of a second conductive material and a portion of said layer of first conductive material; and  
selectively etching a second portion of said layer of a second conductive material.

16. (Currently amended) The method of claim 15 wherein said portion of said layer of a first conductive material substantially corresponds to said first portion of said layer of a second conductive material.

17. (Currently amended) The method of claim 15 further comprising the steps of:  
depositing a layer of a third conductive material onto said layer of a second conductive material; and  
selectively etching a ~~first~~ portion of said layer of a third conductive material.

18. (Currently amended) The method of claim 15 wherein said portion of said layer of a third conductive material substantially corresponds to said portion of said layer of ~~said first~~ a first conductive material and said first portion of said layer of a second conductive material.

19. (Currently amended) A method for fabricating an electrical circuit, comprising the steps of:

depositing a layer of a first conductive material onto a first surface of a substrate;

depositing a layer of a second conductive material onto a second surface of said substrate;

selectively etching a portion of said layer of a first conductive material;

selectively etching a portion of said layer of a second conductive material;

perforating said substrate at a predetermined location; and

electrically coupling said layer of a first conductive material with said layer of a second conductive material via said perforation.

20-25. (Canceled)

26. (New) The method of claim 1 further comprising the step of patterning said layer of a second conductive material to define said portion of said layer of a second conductive material to be etched in connection with said step of etching said layer of a second conductive material.

27. (New) The method of claim 26 further comprising the step of patterning said layer of a first conductive material to define said portion of said layer of a first conductive material to be etched in connection with said step of etching said layer of a first conductive material.

28. (New) The method of claim 1 further comprising the step of patterning said layer of a first conductive material to define said portion of said layer of a first conductive material to be etched in connection with said step of etching said layer of a first conductive material.

29. (New) The method of claim 1 wherein said step of selectively etching said layer of a second conductive material is performed using an etchant that is selected to etch said layer of a second conductive material at a first rate and to etch said layer of a first conductive material at a second rate.

30. (New) The method of claim 29 wherein said second rate is slower than said first rate.

31. (New) The method of claim 1 wherein said step of selectively etching said layer of a second conductive material is performed using an etchant that is selected to etch said layer of a second conductive material and to not substantially etch said layer of a first conductive material.

32. (New) The method of claim 15 further comprising the step of patterning said layer of a second conductive material to define said portion of said layer of a second conductive material and said portion of said layer of a first conductive material to be etched in connection with said step of etching a portion of said layer of a second conductive material and a portion of said layer of a first conductive material.

33. (New) The method of claim 32 further comprising the step of patterning said layer of a first conductive material to define said portion of said layer of a first conductive material to be etched in connection with said step of etching a portion of said layer of a first conductive material.

34. (New) The method of claim 15 further comprising the step of patterning said layer of a first conductive material to define said portion of said layer of a first conductive material to be etched in connection with said step of etching a portion of said layer of a first conductive material.

35. (New) A method for fabricating an electrical circuit, comprising the steps of:

- depositing a layer of a first conductive material onto a surface of a substrate, either directly or in connection with an intermediary layer between said layer of a first conductive material and said surface of a substrate;
- depositing a layer of a second conductive material onto said layer of a first conductive material, either directly or in connection with an interfacial layer between said layer of a second conductive material and said layer of a first conductive material;
- selectively etching a portion of said layer of a second conductive material;
- selectively etching a portion of said layer of a first conductive material.

36. (New) The method of claim 35 wherein an interfacial layer is deposited between said layer of a second conductive material and said layer of a first conductive material, further comprising the step of selectively etching a portion of said interfacial layer.

37. (New) The method of claim 36 wherein said steps of selectively etching a portion of said layer of a second conductive material and selectively etching a portion of said interfacial layer are performed substantially simultaneously.

38. (New) The method of claim 36 wherein said steps of selectively etching a portion of said layer of a second conductive material, selectively etching a portion of said interfacial layer; and selectively etching a portion of said layer of a first conductive material comprise:

selectively etching a first portion of said layer of a second conductive material, a portion of said interfacial layer, and a portion of said layer of a first conductive material; and

selectively etching a second portion of said layer of a second conductive material.

39. (New) The method of claim 35 wherein said step of etching said layer of a second conductive material is performed using an etchant that etches said layer of a second conductive material at a first rate and that etches said layer of a first conductive material at a second rate.

40. (New) The method of claim 39 wherein said second rate is slower than said first rate.

41. (New) The method of claim 36 wherein said step of etching said layer of a second conductive material is performed using an etchant that etches said layer of a second conductive material at a first rate and that does not substantially etch said layer of a first conductive material.

42. (New) The method of claim 35 wherein said step of etching said layer of a second conductive material is performed using an etchant that etches said layer of a second conductive

material at a first rate, that etches said interfacial layer at a second rate, and that etches said layer of a first conductive material at a third rate.

43. (New) The method of claim 42 wherein said third rate is slower than said first rate and said second rate.

44. (New) The method of claim 15 further comprising the step of depositing an interfacial layer between said layer of a first conductive material and said layer of a second conductive material.